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Docket: AM-3245

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Date: Dec 27, 2001

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hoiman HUNG et al.

Attorneys Docket: AM-3245

Serial No.: 09/276,376

Art Unit No.: 1746

Filed: March 25, 1999

Examiner: A. Olsen

For: "ENHANCEMENT OF SILICON OXIDE ETCH RATE AND SUBSTRATE SELECTIVITY WITH XENON ADDITION"

Commissioner of Patents and Trademarks
Washington, DC 20231

AMENDMENT UNDER 37 CFR §1.111

Sir:

In response to the Office Action of September 10, 2001, please amend the above application as follows:

In the specification:

Paragraph at page 5, lines 2-16:

An example of an inductively coupled plasma etch reactor is the Inductive Plasma Source (IPS) etch reactor, which is available from Applied Materials and which Collins et al. describe in U.S. Patent Application, Serial No. 08/733,544, filed October 21, 1996 and in European Patent Publication EP-840,365-A2. As shown in FIG. 3, a wafer 30 to be processed is closely supported

